IN THE CLAIMS

Claims 8-18 have previously been cancelled without prejudice as being drawn to a non-elected invention.

Please amend claims 1 and 19.

Please withdraw claims 24 - 26 without prejudice.

Please enter the pending claims as follows:

1. (Currently Amended) A device comprising a multilayer stack of thin films, said thin films comprising a low-dielectric constant material, said thin films having pores, wherein each thin film within said multilayer stack has a thickness of less than about 14.0 nm, wherein different porogens or organic components may be used to form different thin films ~~20.0% of critical dimension (CD) of features in said devices~~.

2. (Original) The structure of claim 1 wherein said low-dielectric constant material comprises an inorganic oxide.

3. (Original) The structure of claim 2 wherein said inorganic oxide comprises Silicon Dioxide or silica.

4. (Original) The structure of claim 1 wherein said thin films have a porosity of below about 30.0 volume %.

5. (Original) The structure of claim 1 wherein said pores are embedded within said thin films.

6. (Original) The structure of claim 1 wherein said pores are unconnected.

7. (Original) The structure of claim 1 wherein said pores have a size on the order of 0.3-3.0 nanometers.

8. - 18. (Cancelled)

19. (Currently Amended) A multilevel interconnect system for a device comprising:

an underlying metal level;

a multilayer stack disposed over said underlying metal level, said multilayer stack comprising:

thin films, said thin films having a low dielectric constant, said thin films having pores, wherein said ~~each~~ thin films are formed with a chemical vapor deposition process with reactants that include a porogen or

precursor having 10.0-25.0 weight % organic components ~~film has a thickness of less than 20.0% of critical dimension (CD) of features in said device~~; and

an overlying metal level disposed over said multilayer stack.

20. (Previously Presented) The multilevel interconnect system of claim 19 wherein said thin films have a porosity of below about 30.0 volume %.

21. (Previously Presented) The multilevel interconnect system of claim 19 wherein said pores are embedded within said thin films.

22. (Original) The multilevel interconnect system of claim 19 wherein said pores are unconnected.

23. (Original) The multilevel interconnect system of claim 19 wherein said pores have a size on the order of 0.3-3.0 nanometers.

24. (Withdrawn) A low-dielectric constant structure comprising a multilayer stack of thin films, said multilayer stack remaining stable up to 425.0 degrees Centigrade, said thin films comprising: an upper surface pore, an embedded pore, a lower surface pore, and a through pore, wherein said upper surface pores and said lower surface pores do not stack up over each other consecutively for more than 3 of said thin films.

25. (Withdrawn) The low-dielectric constant structure of claim 24 wherein said thin films have a porosity of below 30.0 volume %.

26. (Withdrawn) The low-dielectric constant structure of claim 24 wherein said pores have a size on the order of 0.3-3.0 nanometers.